
Chipsmall
深圳市津利帝科技有限公司
Geelead Technology Limited
Chipsmall
采购部

ALPHA & OMEGA SEMICONDUCTOR

AOT292L/AOB292L/AOTF292L

100V N-Channel AlphaSGT™

General Description

- Trench Power AlphaSGT™ technology
- Low $R_{DS(ON)}$
- RoHS and Halogen Free Compliant

Product Summary

V_{DS}	100V	
I_D (at V_{GS}=10V)	105A	
$R_{DS(ON)}$ (at V_{GS}=10V)	< 4.5mΩ	(< 4.1mΩ*)
$R_{DS(ON)}$ (at V_{GS}=6V)	< 5.3mΩ	(< 4.9mΩ*)

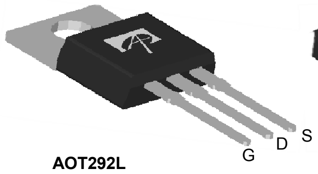
100% UIS Tested
100% Rg Tested

Applications

- Synchronous Rectification for power supply
- Ideal for boost converters

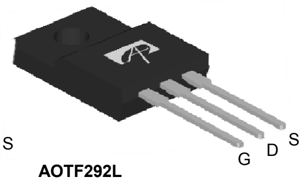
Top View

TO-220



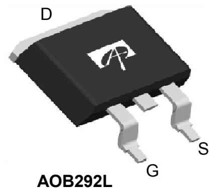
AOT292L

TO-220F

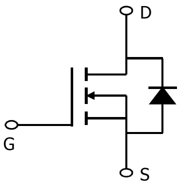


AOTF292L

TO-263



AOB292L



Orderable Part Number	Package Type	Form	Minimum Order Quantity
AOT292L	TO-220	Tube	1000
AOTF292L	TO-220F	Tube	1000
AOB292L	TO-263	Tape & Reel	800

Absolute Maximum Ratings T_A=25°C unless otherwise noted

Parameter		Symbol	AOT(B)292L	AOTF292L	Units
Drain-Source Voltage		V_{DS}	100		V
Gate-Source Voltage		V_{GS}	±20		V
Continuous Drain Current [G**]	T_C=25°C	I_D	105	70	A
	T_C=100°C		82	50	
Pulsed Drain Current [C]		I_{DM}	420		
Continuous Drain Current	T_A=25°C	I_{DSM}	14.5		A
	T_A=70°C		11.5		
Avalanche Current [C]		I_{AS}	60		A
Avalanche energy [C]	L=0.1mH	E_{AS}	180		mJ
V_{DS} Spike	10µs	V_{SPIKE}	120		V
Power Dissipation [B]	T_C=25°C	P_D	300	47	W
	T_C=100°C		150	23	
Power Dissipation [A]	T_A=25°C	P_{DSM}	2.1		W
	T_A=70°C		1.3		
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 175		°C

Thermal Characteristics

Parameter		Symbol	AOT(B)292L	AOTF292L	Units
Maximum Junction-to-Ambient [A]	t ≤ 10s	$R_{\theta JA}$	15		°C/W
Maximum Junction-to-Ambient [A D]	Steady-State		60		°C/W
Maximum Junction-to-Case	Steady-State	$R_{\theta JC}$	0.5	3.2	°C/W

* Surface mount package TO263
** Package limited for TO220 & TO263

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	ID=250µA, V_{GS}=0V	100			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=100V, V_{GS}=0V			1	µA
		T_J=55°C			5	
I_{GSS}	Gate-Body leakage current	V_{DS}=0V, V_{GS}=±20V			±100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=$V_{GS,}$ I_D=250µA	2.3	2.8	3.4	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V, I_D=20A		3.7	4.5	mΩ
		TO220/TO220F T_J=125°C		6.1	7.4	
		V_{GS}=6V, I_D=20A TO220/TO220F		4.2	5.3	mΩ
		V_{GS}=10V, I_D=20A TO263		3.3	4.1	mΩ
		V_{GS}=6V, I_D=20A TO263		3.8	4.9	mΩ
g_{FS}	Forward Transconductance	V_{DS}=5V, I_D=20A		90		S
V_{SD}	Diode Forward Voltage	I_S=1A, V_{GS}=0V		0.68	1	V
I_S	Maximum Body-Diode Continuous Current(TO220/TO263) G				105	A
	Maximum Body-Diode Continuous Current(TO220F)				50	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=50V, f=1MHz		6775		pF
C_{oss}	Output Capacitance			557		pF
C_{rss}	Reverse Transfer Capacitance			32		pF
R_g	Gate resistance	f=1MHz	0.4	0.8	1.2	Ω
SWITCHING PARAMETERS						
Q_g(10V)	Total Gate Charge	V_{GS}=10V, V_{DS}=50V, I_D=20A		90	126	nC
Q_g(4.5V)	Total Gate Charge			40	60	nC
Q_{gs}	Gate Source Charge			24		nC
Q_{gd}	Gate Drain Charge			13.5		nC
$t_{D(on)}$	Turn-On DelayTime	V_{GS}=10V, V_{DS}=50V, R_L=2.5Ω, R_{GEN}=3Ω		20		ns
t_r	Turn-On Rise Time			11.5		ns
$t_{D(off)}$	Turn-Off DelayTime			48		ns
t_f	Turn-Off Fall Time			10		ns
t_{rr}	Body Diode Reverse Recovery Time	I_F=20A, di/dt=500A/µs		50		ns
Q_{rr}	Body Diode Reverse Recovery Charge	I_F=20A, di/dt=500A/µs		380		nC

A. The value of $R_{\theta JA}$ is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A =25° C. The Power dissipation P_{DSM} is based on R $_{\theta JA}$ t≤ 10s and the maximum allowed junction temperature of 150° C. The value in any given application depends on the user's specific board design, and the maximum temperature of 175° C may be used if the PCB allows it.
B. The power dissipation P_D is based on $T_{J(MAX)}$=175° C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.
C. Single pulse width limited by junction temperature $T_{J(MAX)}$=175° C.
D. The $R_{\theta JA}$ is the sum of the thermal impedance from junction to case $R_{\theta JC}$ and case to ambient.
E. The static characteristics in Figures 1 to 6 are obtained using <300µs pulses, duty cycle 0.5% max.
F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of $T_{J(MAX)}$=175° C. The SOA curve provides a single pulse rating.
G. The maximum current rating is package limited.
H. These tests are performed with the device mounted on 1 in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A=25° C.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

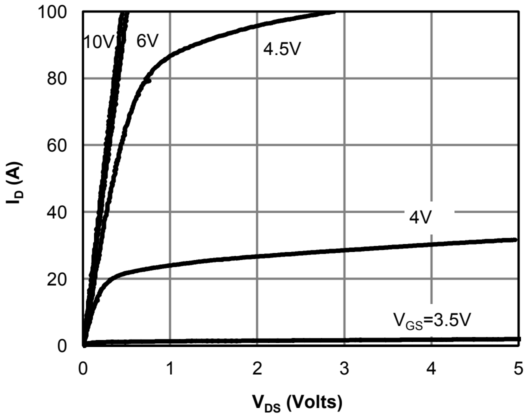


Figure 1: On-Region Characteristics (Note E)

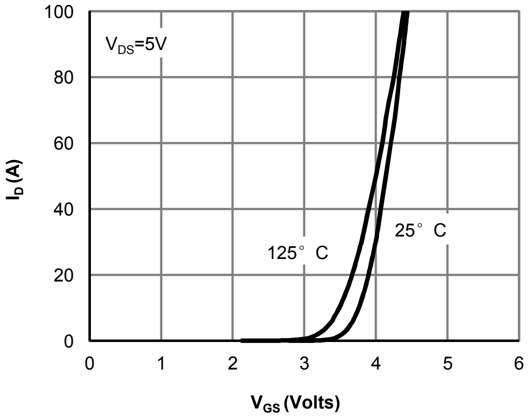


Figure 2: Transfer Characteristics (Note E)

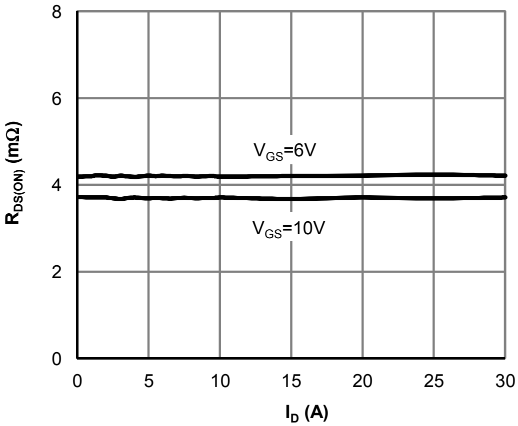


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

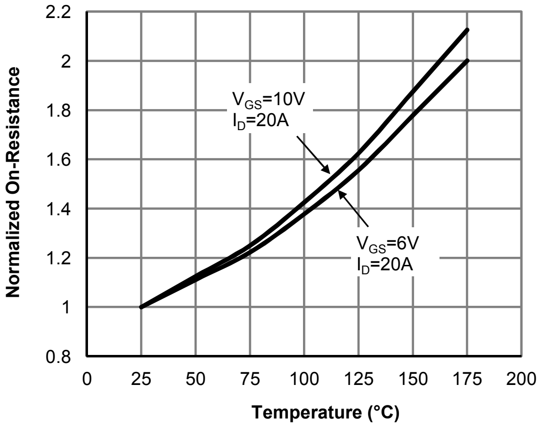


Figure 4: On-Resistance vs. Junction Temperature (Note E)

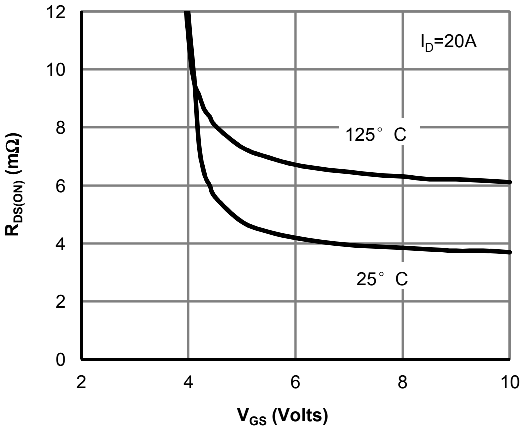


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

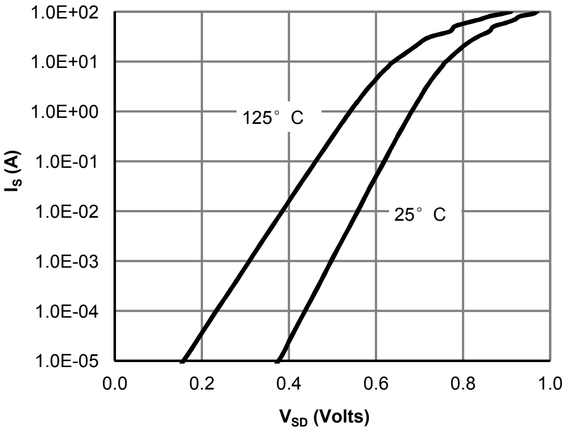


Figure 6: Body-Diode Characteristics (Note E)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

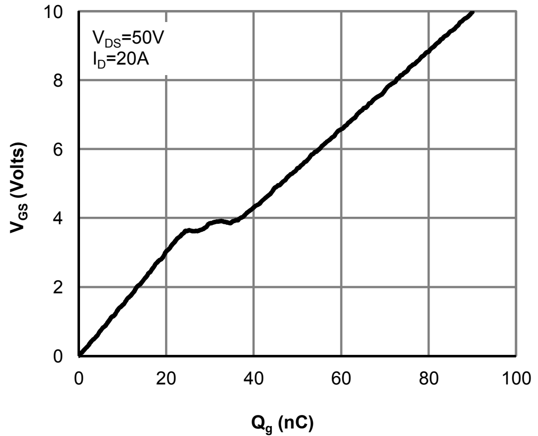


Figure 7: Gate-Charge Characteristics

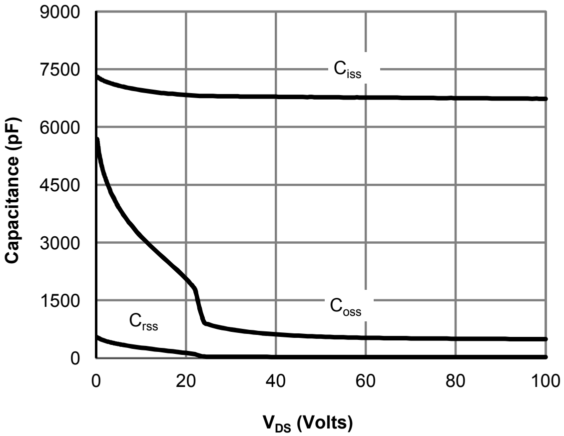
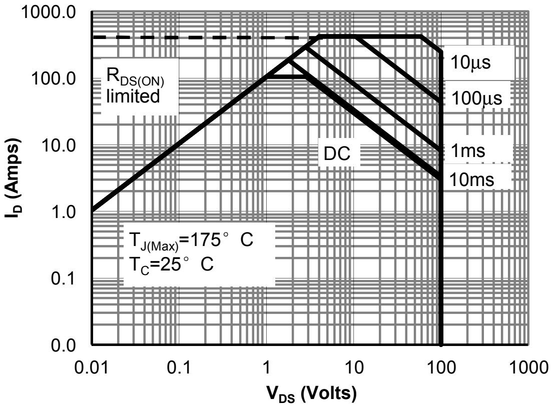


Figure 8: Capacitance Characteristics



V_{GS}> or equal to 6V
Figure 9A: Maximum Forward Biased Safe Operating Area for TO220 & TO263 (Note F)

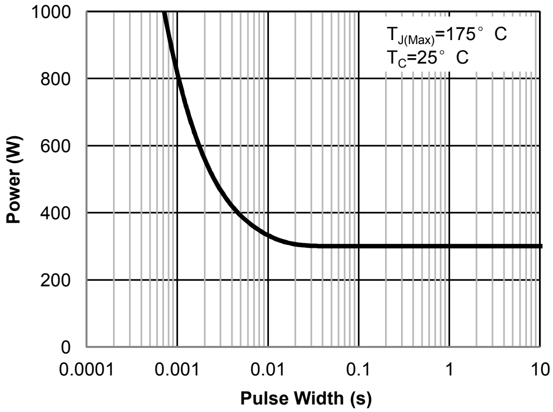
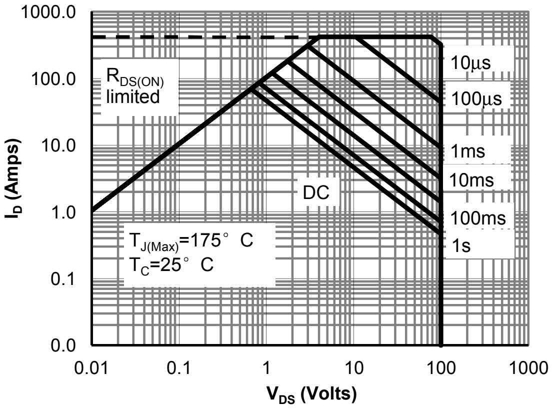


Figure 10A: Single Pulse Power Rating Junction-to-Case for TO220 & TO263 (Note F)



V_{GS}> or equal to 6V
Figure 9B: Maximum Forward Biased Safe Operating Area for TO220F (Note F)

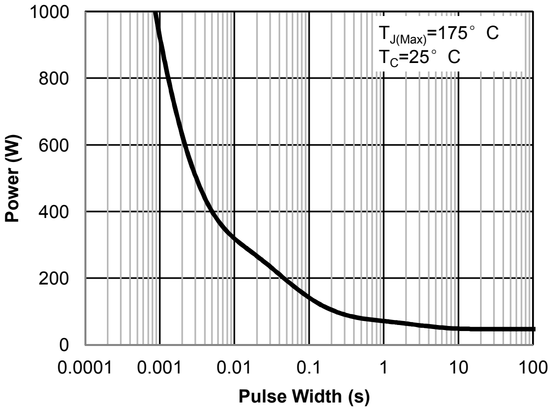


Figure 10B: Single Pulse Power Rating Junction-to-Case for TO220F (Note F)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

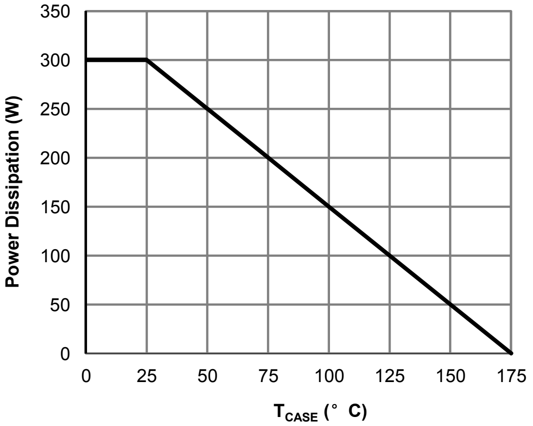


Figure 11A: Power De-rating for TO220 & TO263 (Note F)

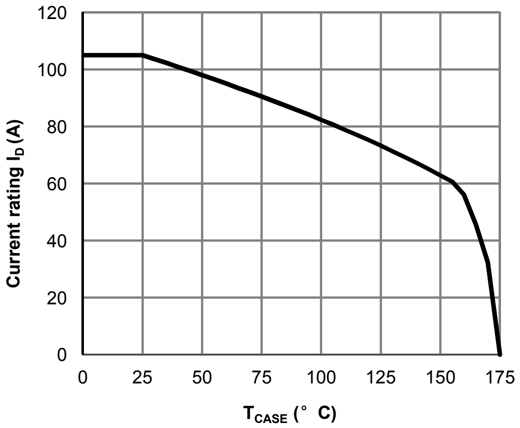


Figure 12A: Current De-rating for TO220 & TO263 (Note F)

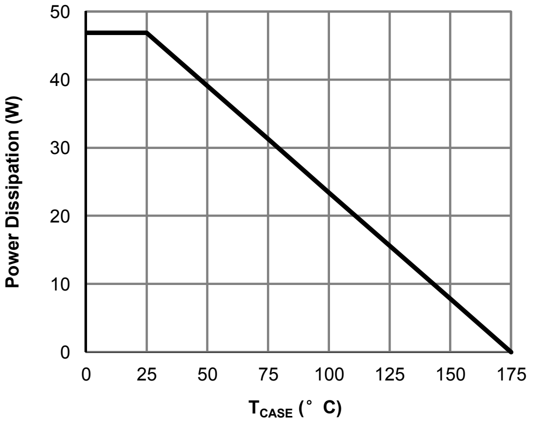


Figure 11B: Power De-rating for TO220F (Note F)

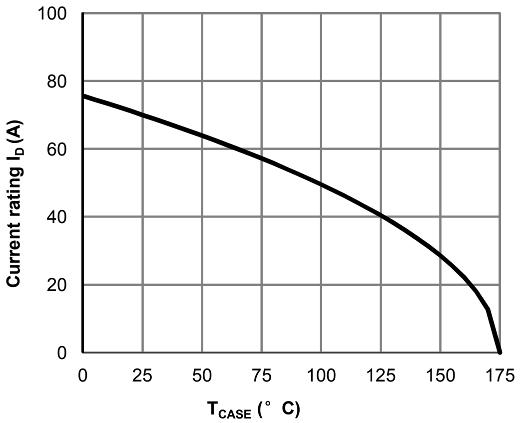


Figure 12B: Current De-rating for TO220F (Note F)

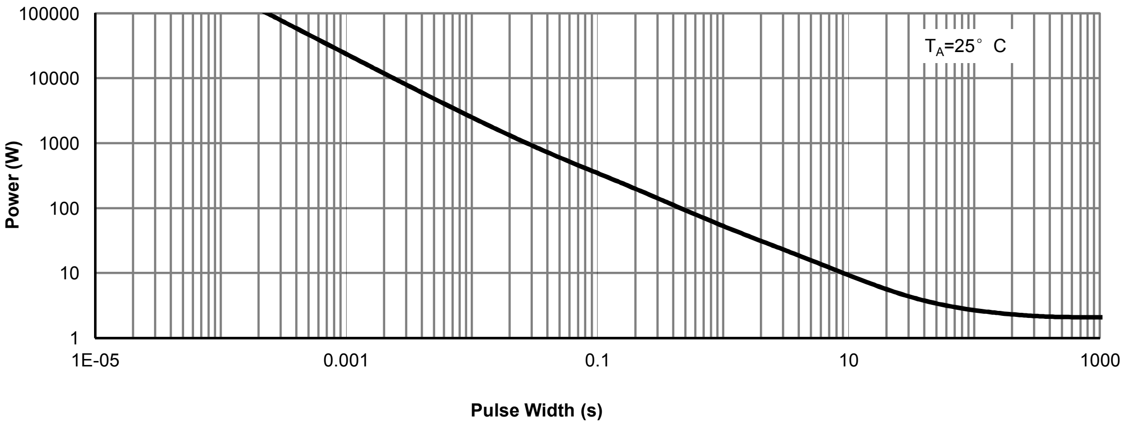


Figure 13: Single Pulse Power Rating Junction-to-Ambient (Note H)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

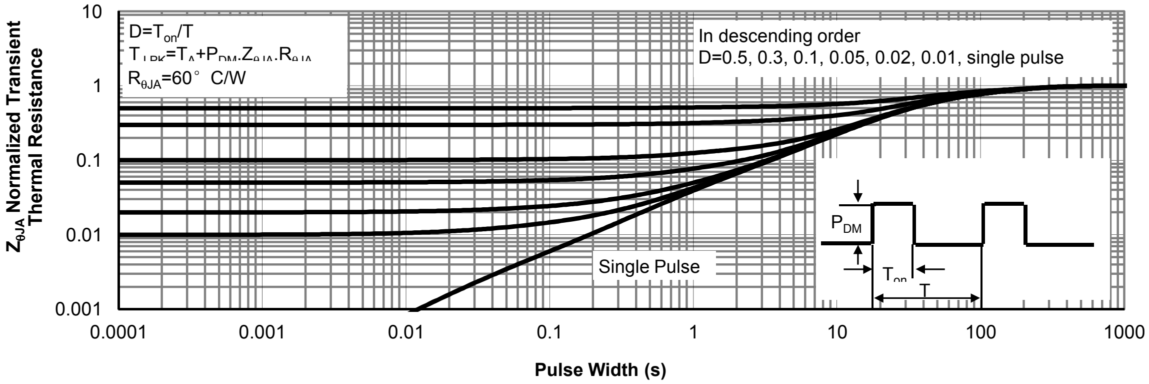


Figure 14: Normalized Maximum Transient Thermal Impedance (Note H)

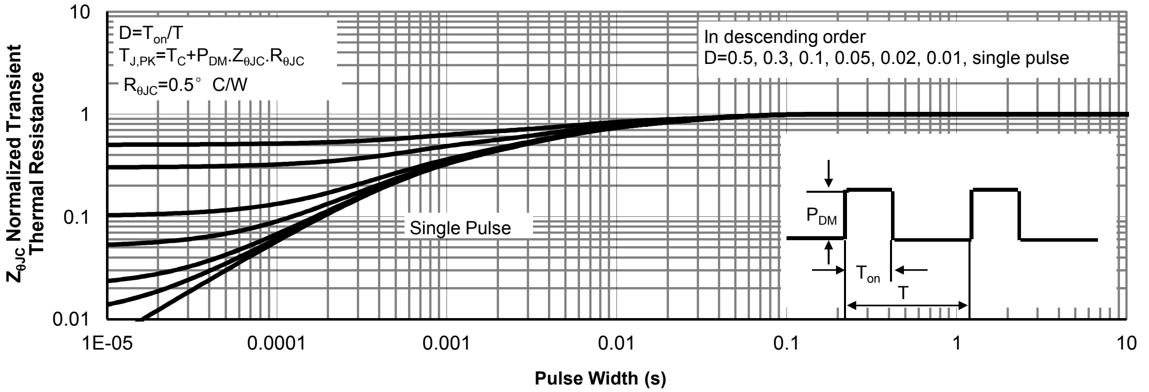


Figure 15A: Normalized Maximum Transient Thermal Impedance for TO220 & TO263 (Note F)

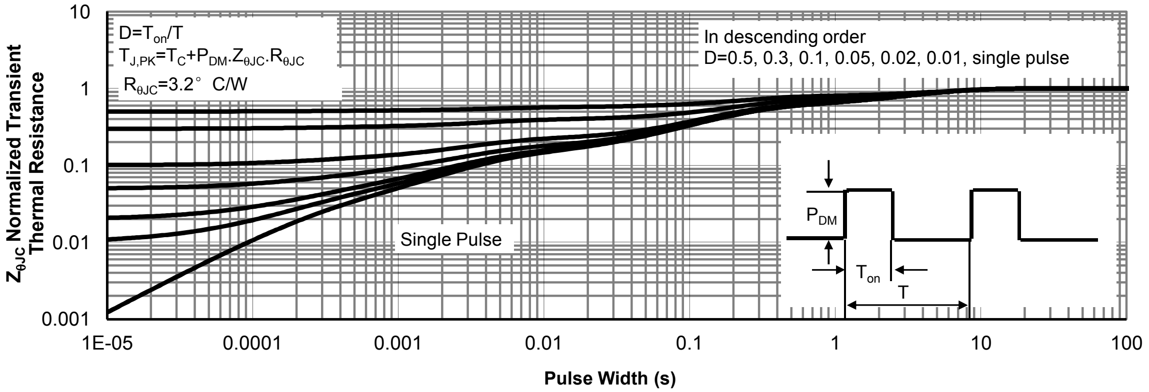


Figure 15B: Normalized Maximum Transient Thermal Impedance for TO220F (Note F)

Figure A: Gate Charge Test Circuit & Waveforms

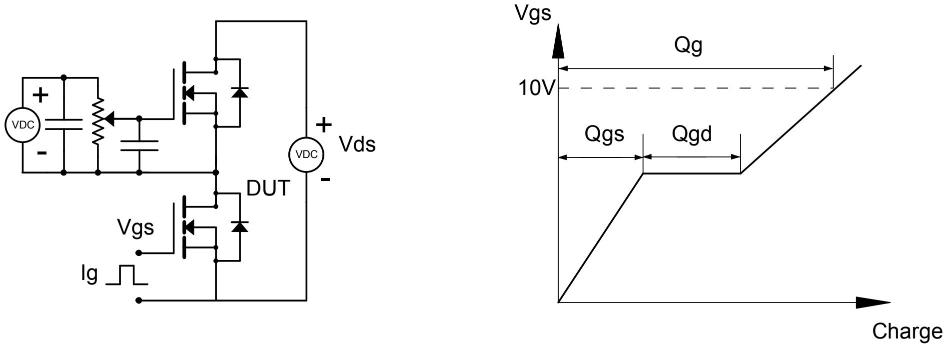


Figure B: Resistive Switching Test Circuit & Waveforms

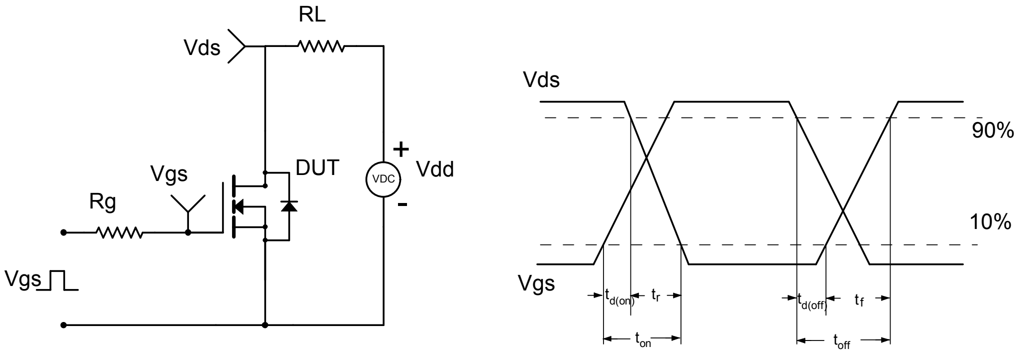


Figure C: Unclamped Inductive Switching (UIS) Test Circuit & Waveforms

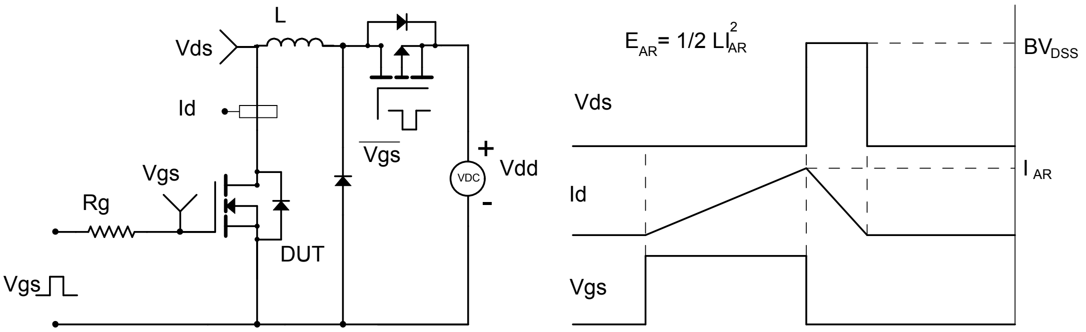


Figure D: Diode Recovery Test Circuit & Waveforms